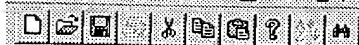


| L Number | Hits | Search Text | DB | Time stamp |
|----------|-------|---|---|------------------|
| - | 23385 | transistor and ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) with gate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:06 |
| - | 6093 | (transistor and ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) with gate)) and (silicon with (wafer substrate)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:11 |
| - | 5427 | ((transistor and ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) with gate)) and (silicon with (wafer substrate))) and (silicon adj nitride nitriding nitrogen nitrogen adj (atmosphere ambient) metal) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 13:35 |
| - | 3752 | ((transistor and ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) with gate)) and (silicon with (wafer substrate))) and (silicon adj nitride nitriding nitrogen nitrogen adj (atmosphere ambient) metal)) and (anneal\$3 heat\$3 thermal) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 13:36 |
| - | 39618 | (method process forming) with metal adj oxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:05 |
| - | 2098 | ((method process forming) with metal adj oxide) and (nitride with (substrate wafer)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:12 |
| - | 2121 | ((method process forming) with metal adj oxide) and ((nitride nitriding nitridation)with (substrate wafer)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 13:47 |
| - | 1055 | ((method process forming) with metal adj oxide) and ((nitride nitriding nitridation)with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2') | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:12 |
| - | 948 | ((method process forming) with metal adj oxide) and ((nitride nitriding nitridation)with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and (anneal\$3 heat\$3 thermal) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:13 |
| - | 88 | ((method process forming) with metal adj oxide) and ((nitride nitriding nitridation)with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and ((anneal\$3 heat\$3 thermal) with laser) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 13:50 |
| - | 65 | ((method process forming) with metal adj oxide) and ((nitride nitriding nitridation)with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and ((anneal\$3 heat\$3 thermal) with laser)) and (silicon with (wafer substrate)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 13:51 |
| - | 5 | ((method process forming) with metal adj oxide) and ((nitride nitriding nitridation)with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and ((anneal\$3 heat\$3 thermal) with laser)) and (silicon with (wafer substrate))) and (atmosphere ambient nitrogen hydrogen source drain s/d)) and (transistor and ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) with gate)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 13:55 |

| | | | | |
|---|-------|--|---|------------------|
| - | 62 | ((((method process forming) with metal adj oxide) and ((nitride nitriding nitridation)with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and ((anneal\$3 heat\$3 thermal) with laser)) and (silicon with (wafer substrate))) and (atmosphere ambient nitrogen hydrogen source drain s/d) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 14:02 |
| - | 16285 | ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near5 gate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:08 |
| - | 13201 | ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near4 gate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:09 |
| - | 9688 | ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near3 gate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:09 |
| - | 5722 | ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near2 gate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:10 |
| - | 2376 | ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:11 |
| - | 761 | ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate)) and ((silicon 'SOI' with (wafer substrate))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:12 |
| - | 199 | ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate)) and ((silicon 'SOI' with (wafer substrate))) and (nitride with (substrate wafer)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:12 |
| - | 92 | ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate)) and ((silicon 'SOI' with (wafer substrate))) and (nitride with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2') | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:13 |
| - | 92 | ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate)) and ((silicon 'SOI' with (wafer substrate))) and (nitride with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and (oxydation oxydiz\$3 oxygen 'O2') | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:13 |
| - | 84 | ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate)) and ((silicon 'SOI' with (wafer substrate))) and (nitride with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and (oxydation oxydiz\$3 oxygen 'O2')) and (anneal\$3 heat\$3 thermal) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:16 |
| - | 8 | ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate)) and ((silicon 'SOI' with (wafer substrate))) and (nitride with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and (oxydation oxydiz\$3 oxygen 'O2')) and (anneal\$3 heat\$3 thermal)) and metal adj oxide) and laser | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:17 |
| - | 58 | ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate)) and ((silicon 'SOI' with (wafer substrate))) and (nitride with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and (oxydation oxydiz\$3 oxygen 'O2')) and (anneal\$3 heat\$3 thermal)) and metal adj oxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/31 15:44 |

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|---|----|---------------|-------|------------------|
| - | 12 | "6020024" | USPAT | 2002/05/31 15:45 |
| - | 1 | "6037235".PN. | USPAT | 2002/05/31 16:07 |
| - | 1 | "6037235".PN. | USPAT | 2002/05/31 16:57 |
| - | 1 | "5716875".PN. | USPAT | 2002/05/31 16:57 |
| - | 1 | "5629043".PN. | USPAT | 2002/05/31 16:57 |
| - | 1 | "6037235".PN. | USPAT | 2002/05/31 16:57 |
| - | 1 | "5716875".PN. | USPAT | 2002/05/31 16:57 |
| - | 1 | "5629043".PN. | USPAT | 2002/05/31 16:57 |
| - | 1 | "5629043".PN. | USPAT | 2002/05/31 16:57 |
| - | 1 | "5591681".PN. | USPAT | 2002/05/31 16:58 |
| - | 1 | "5550091".PN. | USPAT | 2002/05/31 16:58 |
| - | 1 | "5405801".PN. | USPAT | 2002/05/31 16:58 |
| - | 1 | "5405801".PN. | USPAT | 2002/05/31 16:58 |



Active

- ☑ L3: (191) ((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputtering)
- ☑ L4: (2561) nitrogen with (sputtering 'RF' adj3 sputtering)
- ☑ L5: (16) 3 and 4
- ☑ L6: (16) (((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputtering)) and (nit

Failed

☒ Plurals

Default operator: ☐ OR ☒ Highlight all hit terms initially

| | U | I | Document ID | Issue Date | Pages | Title | Current OR | Current XRef |
|----|--------------------------|--------------------------|---------------|------------|-------|--|------------|--------------|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 6537428 B1 | 20030325 | 10 | Stable high rate reactive sputtering | 204/192.13 | 204/192.15; |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 6092669 A | 20000725 | 12 | Equipment for producing thin-film solar cell | 204/298.13 | 204/192.16; |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | US 6048442 A | 20000411 | 12 | Method for producing thin-film solar cell and equipment for producing the | 204/192.28 | 204/192.25 |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | US 5891264 A | 19990406 | 29 | Solar cell and method for producing electrode for solar cell | 136/261 | 204/192.26; |
| 5 | <input type="checkbox"/> | <input type="checkbox"/> | US 5798027 A | 19980825 | 20 | Process for depositing optical thin films on both planar and non-planar s | 204/192.26 | 136/259 |
| 6 | <input type="checkbox"/> | <input type="checkbox"/> | US 5711824 A | 19980127 | 28 | Solar cell | 204/192.26 | 204/192.28; |
| 7 | <input type="checkbox"/> | <input type="checkbox"/> | US 5578501 A | 19961126 | 28 | Method of manufacturing a solar cell by formation of a zinc oxide transpar | 136/259 | 204/192.29; |
| 8 | <input type="checkbox"/> | <input type="checkbox"/> | US 5573884 A | 19961112 | 18 | Image-forming member for electrophotography | 438/98 | 136/256; |
| 9 | <input type="checkbox"/> | <input type="checkbox"/> | US 5420043 A | 19950530 | 29 | Method of manufacturing a solar cell | 430/126 | 204/192.14; |
| 10 | <input type="checkbox"/> | <input type="checkbox"/> | US 5401330 A | 19950328 | 58 | Photovoltaic element | 438/96 | 204/192.29; |
| | | | | | | | | 427/528; |
| | | | | | | | | 136/249; |
| | | | | | | | | 136/258 |

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NUM

- 3 L3: (191) ((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputtering)
- 3 L4: (2561) nitrogen with (sputtering 'RF' adj3 sputtering)
- 3 L5: (16) 3 and 4
- 3 L6: (16) (((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputtering)) and (nit

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Default operator: ☐ OR ☒ Highlight all hit terms initially

(((solar photovoltaic) near3

| | U | I | Document ID | Issue Date | Pages | Title | Current OR | Current XRef |
|----|--------------------------|--------------------------|--------------|------------|-------|---|------------|----------------------------|
| 8 | <input type="checkbox"/> | <input type="checkbox"/> | US 5573884 A | 19961112 | 18 | Image-forming member for electrophotography | 430/126 | 430/95 |
| 9 | <input type="checkbox"/> | <input type="checkbox"/> | US 5420043 A | 19950530 | 29 | Method of manufacturing a solar cell | 438/96 | 204/192.29; 427/528; |
| 10 | <input type="checkbox"/> | <input type="checkbox"/> | US 5401330 A | 19950328 | 58 | Photovoltaic element | 136/259 | 136/249; 136/258; |
| 11 | <input type="checkbox"/> | <input type="checkbox"/> | US 5324365 A | 19940628 | 25 | Solar cell | 136/256 | 136/258; 136/259; |
| 12 | <input type="checkbox"/> | <input type="checkbox"/> | US 5225057 A | 19930706 | 21 | Process for depositing optical films on both planar and non-planar substr | 204/192.13 | 204/192.12; 204/192.26 |
| 13 | <input type="checkbox"/> | <input type="checkbox"/> | US 4844719 A | 19890704 | 22 | Permeable polymer membrane for dessication of gas | 95/52 | 204/296; 521/27; |
| 14 | <input type="checkbox"/> | <input type="checkbox"/> | US 4673476 A | 19870616 | 6 | Antireflective film for photoelectric devices and manufacturing method th | 204/192.28 | 204/192.12; 204/192.15; |
| 15 | <input type="checkbox"/> | <input type="checkbox"/> | US 4511756 A | 19850416 | 4 | Amorphous silicon solar cells and a method of producing the same | 136/258 | 136/256; 204/192.25; |
| 16 | <input type="checkbox"/> | <input type="checkbox"/> | US 4471042 A | 19840911 | 24 | Image-forming member for electrophotography comprising hydro | 430/64 | 136/258; 252/501.1; |



Active

- ☞ L3: (191) ((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputtering)
- ☞ L4: (2561) nitrogen with (sputtering 'RF' adj3 sputtering)
- ☞ L5: (16) 3 and 4
- ☞ L6: (16) (((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputtering)) and (nit

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| 3 and 4 | | | |

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|----|--------------------------|--------------------------|---------------|------------|-------|--|------------|--------------|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 6537428 B1 | 20030325 | 10 | Stable high rate reactive sputtering | 204/192.13 | 204/192.15; |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 6092669 A | 20000725 | 12 | Equipment for producing thin-film solar cell | 204/298.13 | 204/192.16; |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | US 6048442 A | 20000411 | 12 | Method for producing thin-film solar cell and equipment for producing the | 204/192.28 | 204/192.25 |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | US 5891264 A | 19990406 | 29 | Solar cell and method for producing electrode for solar cell | 136/261 | 204/192.26; |
| 5 | <input type="checkbox"/> | <input type="checkbox"/> | US 5798027 A | 19980825 | 20 | Process for depositing optical thin films on both planar and non-planar s | 204/192.26 | 136/256; |
| 6 | <input type="checkbox"/> | <input type="checkbox"/> | US 5711824 A | 19980127 | 28 | Solar cell | 136/259 | 136/259 |
| 7 | <input type="checkbox"/> | <input type="checkbox"/> | US 5578501 A | 19961126 | 28 | Method of manufacturing a solar cell by formation of a zinc oxide transpar | 438/98 | 204/192.28; |
| 8 | <input type="checkbox"/> | <input type="checkbox"/> | US 5573884 A | 19961112 | 18 | Image-forming member for electrophotography | 430/126 | 204/192.29; |
| 9 | <input type="checkbox"/> | <input type="checkbox"/> | US 5420043 A | 19950530 | 29 | Method of manufacturing a solar cell | 438/96 | 438/609; |
| 10 | <input type="checkbox"/> | <input type="checkbox"/> | US 5401330 A | 19950328 | 58 | Photovoltaic element | 136/259 | 430/95 |

☒ Hits
 ☒ Details
 ☐ HTML

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File View Edit Tools Window Help

Active

L3: (191) ((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputtering)

L4: (2561) nitrogen with (sputtering 'RF' adj3 sputtering)

L5: (16) 3 and 4

L6: (16) (((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputtering)) and (nit

Failed

Browse Queue Clear

DB: USPAT ☒ Plurals

Default operator: ☐ Highlight all hit terms initially

3 and 4

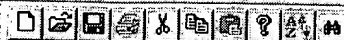
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| | U | I | Document ID | Issue Date | Pages | Title | Current OR | Current XRef |
|----|--------------------------|--------------------------|--------------|------------|-------|---|------------|--------------|
| 8 | <input type="checkbox"/> | <input type="checkbox"/> | US 5573884 A | 19961112 | 18 | Image-forming member for electrophotography | 430/126 | 430/95 |
| 9 | <input type="checkbox"/> | <input type="checkbox"/> | US 5420043 A | 19950530 | 29 | Method of manufacturing a solar cell | 438/96 | 204/192.29; |
| 10 | <input type="checkbox"/> | <input type="checkbox"/> | US 5401330 A | 19950328 | 58 | Photovoltaic element | 136/259 | 427/528; |
| 11 | <input type="checkbox"/> | <input type="checkbox"/> | US 5324365 A | 19940628 | 25 | Solar cell | 136/256 | 136/249; |
| 12 | <input type="checkbox"/> | <input type="checkbox"/> | US 5225057 A | 19930706 | 21 | Process for depositing optical films on both planar and non-planar substr | 204/192.13 | 136/258; |
| 13 | <input type="checkbox"/> | <input type="checkbox"/> | US 4844719 A | 19890704 | 22 | Permeable polymer membrane for dessication of gas | 95/52 | 136/258; |
| 14 | <input type="checkbox"/> | <input type="checkbox"/> | US 4673476 A | 19870616 | 6 | Antireflective film for photoelectric devices and manufacturing method th | 204/192.28 | 136/259; |
| 15 | <input type="checkbox"/> | <input type="checkbox"/> | US 4511756 A | 19850416 | 4 | Amorphous silicon solar cells and a method of producing the same | 136/258 | 204/192.12; |
| 16 | <input type="checkbox"/> | <input type="checkbox"/> | US 4471042 A | 19840911 | 24 | Image-forming member for electrophotography comprising hydro | 430/64 | 204/192.15; |
| | | | | | | | | 136/256; |
| | | | | | | | | 204/192.25; |
| | | | | | | | | 136/258; |
| | | | | | | | | 252/501.1; |

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- ☑ L4: (7) ((solar photovoltaic) near3 cell) with (('II-VI' 'CdTe' cadmium adj te
- ☑ L6: (183) ((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputteri
- ☑ L7: (15) 6 and (nitrogen with (sputtering 'RF' adj3 sputtering))
- ☑ L8: (68) ((solar photovoltaic) near3 cell) with ('II-VI')
- ☑ L9: (11917) ((solar photovoltaic) near3 cell)
- ☑ L10: (87) 9 and (nitrogen with (sputtering 'RF' adj3 sputtering))
- ☑ L11: (34) 10 and (nitrogen cadmium telluride sulfide selenide Zinc)
- ☑ L12: (0) (inert with sputtering) with (solar photovoltaic)
- ☑ L13: (1949) (inert with sputtering)
- ☑ L14: (0) (inert with sputtering) with Cadmium
- ☑ L15: (0) (inert with sputtering) same Cadmium
- ☑ L16: (0) (nitrogen with sputtering) same Cadmium
- ☑ L17: (31) (nitrogen with sputtering) same metallization

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Search List Browse Queue Clear

DBs: USPAT ☒ Plurals

Default operator: OR ☒ Highlight all hit terms initially

(nitrogen with sputtering) same metallization









BRS form IS&R form Image Text HTML

| | U | I | Document ID | Issue Date | Pages | Title | Current OR | Current XRef |
|---|-------------------------------------|--------------------------|---------------|------------|-------|--|------------|--------------|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 6309967 B1 | 20011030 | 12 | Method of forming a contact | 438/658 | 438/656; |
| 2 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 6306762 B1 | 20011023 | 9 | Semiconductor device having | 438/648 | 438/661; |
| 3 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 6296747 B1 | 20011002 | 9 | multi-layered metalization and method | | 438/653; |
| 4 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 6255671 B1 | 20010703 | 10 | Baffled perforated shield in a plasma | 204/298.07 | 438/656 |
| 5 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 6239029 B1 | 20010529 | 13 | sputtering reactor | | 204/298.11; |
| | | | | | | Metal embedded passivation layer | 257/103 | 204/298.14 |
| | | | | | | structure for microelectronic intercon | | 257/613; |
| | | | | | | Sacrificial germanium layer for | 438/688 | 257/615; |
| | | | | | | | | 438/658; |

Hits Details HTML

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-  Drafts
-  Pending
-  Active
 -  L1: (4) "5393675"
 -  L2: (1) "5304499".PN.
 -  L3: (1) "4650921".PN.
 -  L5: (3) 4 and nitrogen
 -  L4: (7) ((solar photovoltaic) near3 cell) with ((

The screenshot shows a web-based search interface. At the top, there are buttons for 'Search', 'List', 'Browse', 'Queue', and 'Clear'. Below these is a search bar containing the text 'DBs USPAT'. To the right of the search bar are two checkboxes: 'Plurals' (checked) and 'Highlight all hit terms initially' (checked). Below the search bar is a label 'Default operator:' followed by a dropdown menu showing 'OR'. The main search results area contains a single entry: '((solar photovoltaic near3 cell) with ((II-VT 'CdTe' cadmium adj telluride) with (sputtering 'RF' adj3 sputtering)))'. At the bottom of the interface, there is a navigation bar with icons and labels for 'BRS form', 'IS&R', 'Image', 'Text', and 'HTML'.

Search [List] [Browse] [Queue] [Clear]

DBs USPAT ☒ Plurals ☒ Highlight all hit terms initially

Default operator: OR

((solar photovoltaic near3 cell) with ((II-VT 'CdTe' cadmium adj telluride) with (sputtering 'RF' adj3 sputtering)))

BRS form IS&R Image Text HTML

| | U | I | Document ID | Issue Date | Pages | Title | Current OR | Current XRef | R |
|---|-------------------------------------|--------------------------|--------------|------------|-------|--|------------|----------------------|---|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 6137048 A | 20001024 | 14 | Process for fabricating polycrystalline semiconductor thin-film solar cells, a | 136/260 | 136/256; 136/265; | |
| 2 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5714404 A | 19980203 | | Fabrication of polycrystalline thin films by pulsed laser processing | 438/94 | 438/487; 438/798; | |
| 3 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5500056 A | 19960319 | | Solar cell containing low melting point glass layer | 136/259 | 136/256; 136/260; | |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | US 5393675 A | 19950228 | 8 | Process for RF sputtering of cadmium telluride photovoltaic cell | 438/95 | 136/260; 136/264; | |
| 5 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 4345107 A | 19820817 | 13 | Cadmium telluride photovoltaic cells | 136/255 | 136/260; 136/264; | |
| 6 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 4261802 A | 19810414 | 9 | Method of making a photovoltaic cell | 438/92 | 136/260; 205/170; | |
| 7 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 4260427 A | 19810407 | 8 | CdTe Schottky barrier photovoltaic cell | 136/255 | 136/260; 257/110; | |